

SEMICONDUCTOR TECHNICAL DATA

KTA200

EPITAXIAL PLANAR PNP TRANSISTOR

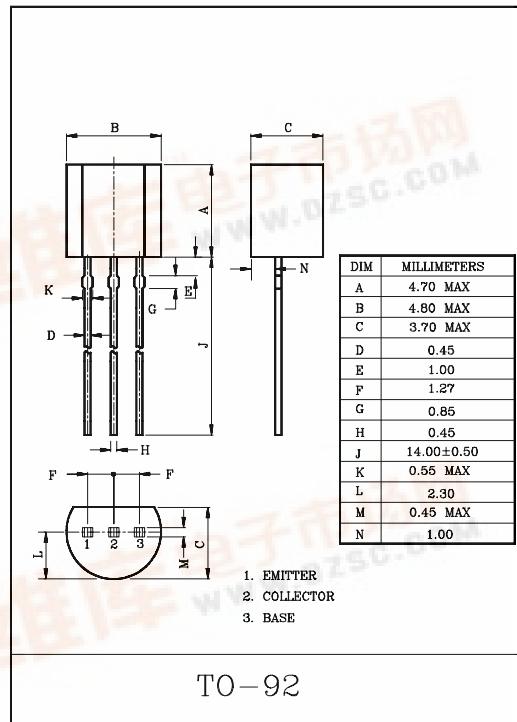
GENERAL PURPOSE APPLICATION,
SWITCHING APPLICATION.

FEAUTRES

- Excellent h_{FE} Linearity
: $h_{FE}(2)=25(\text{Min.})$ at $V_{CE}=-6V$, $I_C=-400mA$.
- Complementary to KTC200.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Base Current	I_B	-100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-50V$, $I_E=0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V$, $I_C=0$	-	-	-0.1	μA
DC Current Gain (Note)	$h_{FE}(1)$	$V_{CE}=-2V$, $I_C=-50mA$	70	-	240	
	$h_{FE}(2)$	$V_{CE}=-6V$, $I_C=-400mA$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$, $I_B=-10mA$	-	-0.1	-0.25	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-1V$, $I_C=-100mA$	-	-0.8	-1.0	V
Transition Frequency	f_T	$V_{CE}=-6V$, $I_C=-20mA$	-	200	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6V$, $I_E=0$, $f=1MHz$	-	13	-	pF

Note : $h_{FE}(1)$ Classification O:70~140 , Y:120~240

KTA200

